



45V NPN SMALL SIGNAL TRANSISTOR IN DFN0806

Features

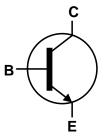
- $BV_{CEO} > 45V$
- I_C = 100mA High Collector Current
- P_D = 435mW Power Dissipation
- 0.48mm² Package Footprint, 16 times smaller than SOT23
- 0.4mm Height Package Minimizing Off-Board Profile
- Complementary PNP Type BC857BFA
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

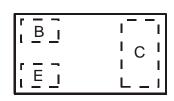
- Case: X2-DFN0806-3
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu, Solderable per MIL-STD-202, Method 208 (e4)
- Weight: 0.0008 grams (Approximate)











Top View Device Schematic

Ordering Information (Note 4)

Top View

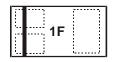
Product		Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
BC847BFA-	7B	1F	7	8mm	10,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

X2-DFN0806-3



Top View Bar Denotes Base and Emitter Side

1F = Product Type Marking Code

Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	50	V
Collector-Emitter Voltage	V _{CEO}	45	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Continuous Collector Current	Ic	100	mA
Peak Pulse Collector Current	I _{CM}	200	mA



Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P_{D}	435	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ hetaJA}$	287	°C/W
Thermal Resistance, Junction to Lead (Note 6)	$R_{ heta JL}$	150	°C/W
Operating and Storage and Temperature Range	T _J , T _{STG}	-55 to +150	°C

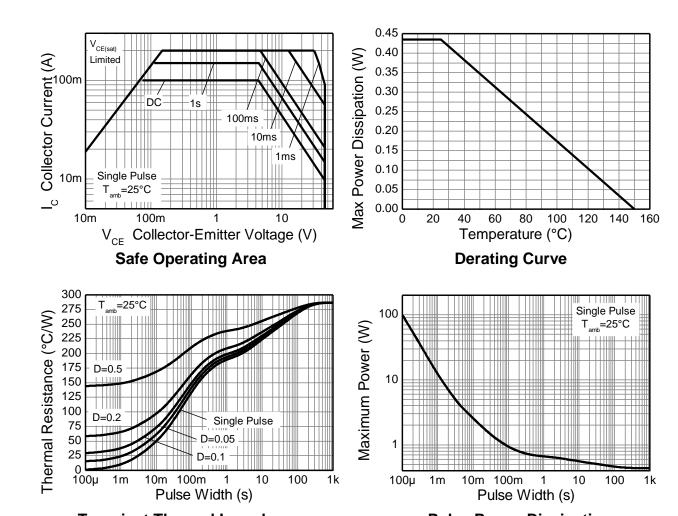
ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	200	V	В

Notes:

- 5. For the device mounted on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady state condition. The entire exposed collector pad is attached to the heatsink.
- 6. Thermal resistance from junction to solder-point (on the exposed collector pad).
- 7. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics and Derating Information



Transient Thermal Impedance

Pulse Power Dissipation



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

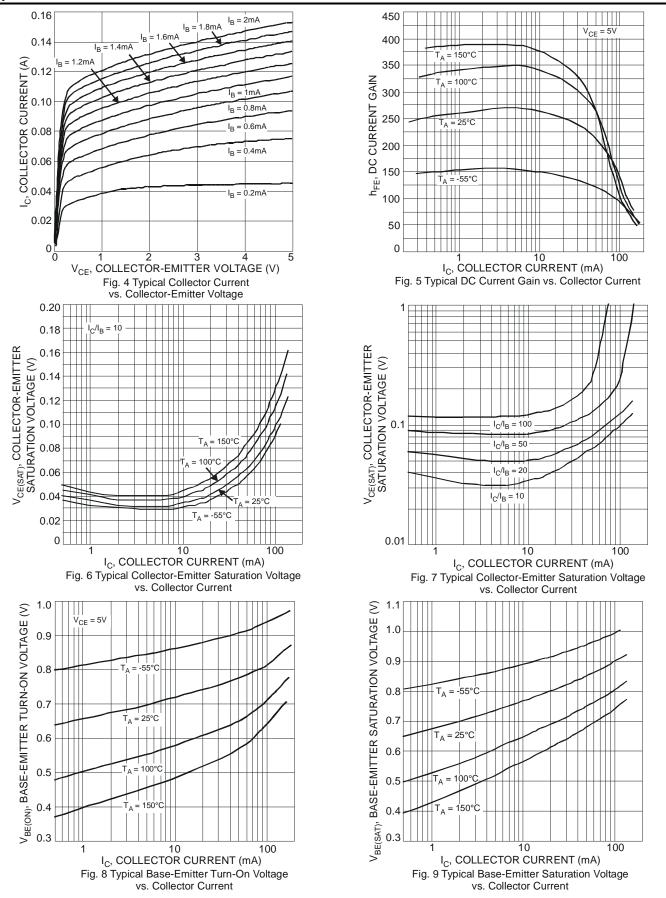
Characteristic	Symbol	Min	Typical	Max	Unit	Test Condition
OFF CHARACTERISTICS	OFF CHARACTERISTICS					
Collector-Base Breakdown Voltage	BV_CBO	50	150	_	V	$I_C = 50\mu A, I_B = 0$
Collector-Emitter Breakdown Voltage	BV _{CES}	50	150	_		$I_C = 50\mu A, I_B = 0$
Collector-Emitter Breakdown Voltage (Note 8)	BV_{CEO}	45	65	_	V	$I_{C} = 1 \text{mA}, I_{B} = 0$
Collector-Base Breakdown Voltage	BV_{EBO}	6.0	8.35	_	V	$I_E = 50\mu A, I_C = 0$
Collector-Base Cut-Off Current	I _{CBO}	_	_	15	nA	$V_{CB} = 40V$
Collector-Emitter Cut-Off Current	Ices	_	_	15	nA	$V_{CE} = 40V$
ON CHARACTERISTICS (Note 8)						
DC Current Gain	h _{FE}	 200	220 260	— 470	_	$I_C = 10\mu A, V_{CE} = 5.0V$ $I_C = 2.0mA, V_{CE} = 5.0V$
Collector-Emitter Saturation Voltage	V _{CE(sat)}	_	50 122	125 300	mV	I _C = 10mA, I _B = 0.5mA I _C = 100mA, I _B = 5.0mA
Base-Emitter Saturation Voltage	V _{BE(sat)}	_	760 880	1000 1100	mV	$I_C = 10\text{mA}, I_B = 0.5\text{mA}$ $I_C = 100\text{mA}, I_B = 5.0\text{mA}$
Base-Emitter Voltage	V _{BE(on)}	580 —	650 725	750 800	mV	$I_C = 2.0 \text{mA}, V_{CE} = 5 \text{V}$ $I_C = 10 \text{mA}, V_{CE} = 5 \text{V}$
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C _{obo}		1.5	_	pF	$V_{CB} = 10.0V$, $f = 1.0MHz$, $I_E = 0$
Current Gain-Bandwidth Product	f _T	100	170	_	MHz	V _{CE} = 5V, I _C = 10mA, f = 100MHz

Note:

8. Measured under pulsed conditions. Pulse width $\leq 300 \mu s.~$ Duty cycle $\leq 2 \%.$



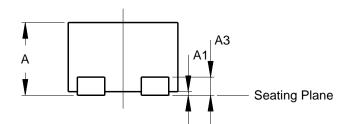
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

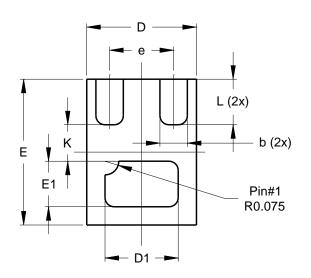




Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

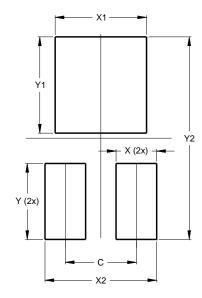




X2-DFN0806-3					
Dim	Min	Max	Тур		
Α	0.375	0.40	0.39		
A1	0	0.05	0.02		
A3	-	-	0.10		
b	0.10	0.20	0.15		
D	0.55	0.65	0.60		
D1	0.35	0.45	0.40		
Е	0.75	0.85	0.80		
E1	0.20	0.30	0.25		
е	-	-	0.35		
K	-	-	0.20		
L	0.20	0.30	0.25		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
С	0.350		
Х	0.200		
X1	0.450		
X2	0.550		
Y	0.375		
Y1	0.475		
Y2	1.000		

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